

## REMARKS

Please amend claims 1, 3, 4, 6, 8, 9, 17, 18, 19 and add new claims 21-39 prior to examination of this application in accordance with 37 CFR. 1.115. No new matter has been added.

The Examiner is invited to telephone the below signed attorney to discuss any questions which may remain with respect to the present application.

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### CERTIFICATION UNDER 37 C.F.R. 1.10

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I hereby certify that this Preliminary Amendment and the documents referred to as attached therein are being deposited with the United States Postal Service in an envelope as "Express Mail Post Office to Addressee" service under 37 C.F.R. 1.10 on the date indicated above and is addressed to Assistant Commissioner for Patents, Washington, DC 20231.

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MARKED UP VERSION OF THE CLAIMS

1. (Amended) A method for producing magneto resistive heads comprising the steps of:

positioning at least two magneto resistive elements in spaced relation to one another;

placing the at least two magneto resistive elements in an environment where material is removed [nonselectively] from items in the environment;

monitoring a property of the at least two [of the plurality of] magneto resistive elements; and

[dynamically] covering one of the at least two magneto resistive elements to prevent additional removal of material from the covered magneto resistive element in response to the monitoring step.

3. (Amended) The method of claim 22 wherein the dynamically covering step takes place when the electrical resistance meets a selected level.

4. (Amended) The method of claim [1] 21 wherein the placing step includes placing the at least two magneto resistive elements in an ion milling environment.

6. (Amended) The method of claim [1] 22 wherein the step of dynamically covering one of the at least two of the magneto resistive elements further comprises actuating a shutter to substantially cover one of the at least two magneto resistive elements.

8. (Amended) An apparatus for use in [semiconductor] a wafer process [fabrication] comprising:

a carrier;

an elongated element held by the carrier; and

a [dynamic] mask including a first shutter, a second shutter, and an actuator for moving the first shutter and second shutter, wherein said mask is [that can be] used to selectively cover a first portion of the elongated element as the [semiconductor] wafer process continues to act on a second portion of the elongated element, the [semiconductor] wafer process[es] substantially halting with respect to the first portion of the elongated element.

9. The apparatus of claim 8 wherein the [dynamic] mask is a dynamic mask [further comprises:

a first shutter;  
a second shutter; and

an actuator for moving the first shutter and the second shutter].

17. (Amended) The apparatus of claim 13 wherein the electrical resistance is measured during the [semiconductive] wafer process of ion milling.

18. (Amended) The apparatus of claim 17 wherein the electrical resistance is measured during the [semiconductive] wafer process of ion milling and wherein the controller moves at least one of the first shutter and the second shutter over at least one of the magneto resistive elements during the process of ion milling, wherein the shutter has a width to substantially protect the magneto resistive element below the shutter from removal of material when the shutter is placed in a covering position over the magneto resistive element.

19. (Amended) The apparatus of claim 12, wherein a magneto resistive element selected from the plurality of magneto resistive elements includes a stripe having a stripe height, the resistance measured across the [a] magneto resistive element is related to the stripe height.